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# BIPOLAR ANALOG INTEGRATED CIRCUIT $\mu PC1909$

## SWITCHING REGULATOR CONTROL IC

#### DESCRIPTION

The  $\mu$ PC1909 is a switching regulator control IC ideal for primary side control of active-clamp type<sup>Note</sup> DC/DC converters. This IC has 2 outputs employing a totem-pole circuit with peak output current 1.2 A, and is capable of directly driving a power MOS FET. As a result, it has been possible to realize primary side control of an active-clamp type converter on a single chip.

Note It is necessary to obtain license from Vicor Corporation before using the  $\mu$ PC1909 in an active-clamp type circuit.

#### FEATURES

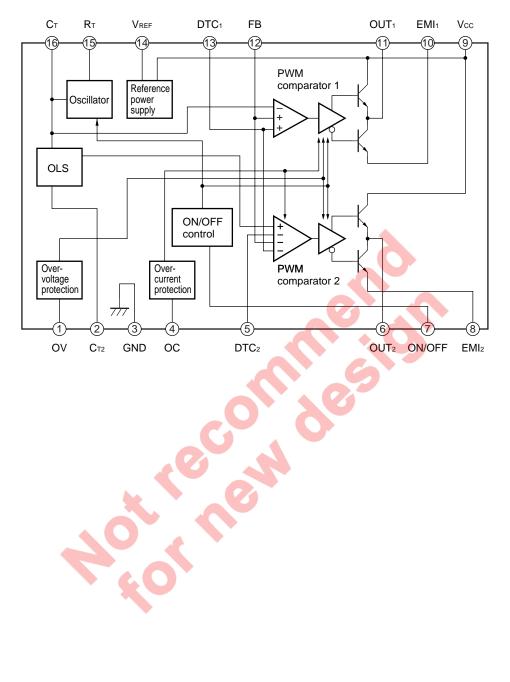
- 2 on-chip outputs; for Q and  $\overline{Q}$
- Capable of directly driving a power MOS FET
- Drive supply voltage range: 7 to 24 V
- On-chip remote control circuit
- On-chip pulse-by-pulse overcurrent protection circuit
- On-chip overvoltage latch circuit

#### **ORDERING INFORMATION**

Part Number	Package
μPC1909CX	16-pin plastic DIP (7.62 mm (300))
$\mu$ PC1909GS	16-pin plastic SOP (7.62 mm (300))

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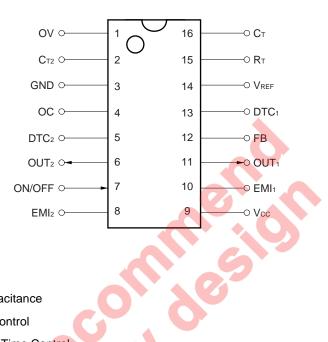
#### **\* BLOCK DIAGRAM**



#### PIN CONFIGURATION (Top View)

16-pin plastic DIP (7.62 mm (300)) μPC1909CX

16-pin plastic SOP (7.62 mm (300)) μPC1909GS



#### ★ Pin Name

Ст	: Timing Capacitance
Ст2	: OLS Shift Control
DTC1	: OUT1 Dead Time Control
DTC <sub>2</sub>	: OUT <sub>2</sub> Dead Time Control
EMI1	: OUT1 Emitter
EMI <sub>2</sub>	: OUT <sub>2</sub> Emitter
FB	: Feedback Input
GND	: Ground
OC	: Over Current Protection
ON/OFF	: ON/OFF Control
OUT1	: OUT1 Output
OUT <sub>2</sub>	: OUT <sub>2</sub> Output
OV	: Over Voltage Protection
Rτ	: Timing Resistance
Vcc	: Power Supply
Vref	: Reference Voltage

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#### **\*** 1. PIN FUNCTION LIST

Pin No.	Symbol	Function
1	OV	Overvoltage protection This is the input pin of the overvoltage detection comparator. Directly connect this pin to GND when not used.
2	Ст2	OLS shift setting The resistor that determines the amount of level shift for dC $\tau$ (an internal triangle wave that is a level-shifted C $\tau$ ) is connected between this pin and the V <sub>REF</sub> pin.
3	GND	Ground This is the signal ground pin.
4	OC	Overcurrent protection This is the input pin of the overcurrent detection comparator. Directly connect this pin to GND when not used.
5	DTC <sub>2</sub>	OUT <sub>2</sub> dead time setting This pins sets the dead time of the OUT <sub>2</sub> output.
6	OUT <sub>2</sub>	OUT <sub>2</sub> output This is the subswitch drive output pin.
7	ON/OFF	ON/OFF control The output circuit can be switched on or off by inputting an external signal. Directly connect this pin to V <sub>REF</sub> when not used.
8	EMI <sub>2</sub>	OUT <sub>2</sub> emitter This is a power supply ground pin. This pin must be isolated from the signal ground pin (GND).
9	Vcc	Power supply
10	EMI1	OUT <sub>1</sub> emitter This is a power supply ground pin. This pin must be isolated from the signal ground pin (GND).
11	OUT <sub>1</sub>	OUT <sub>1</sub> output This is the main switch drive output pin.
12	FB	Feedback input This is the feedback input pin of PWM comparators 1 and 2.
13	DTC <sub>1</sub>	OUT1 dead time setting This pin sets the maximum duty of the OUT1 output and determines the minimum duty of the OUT2 output.
14	Vref	Reference voltage This pin outputs a 4.9-V TYP. reference voltage.
15	Rτ	Timing resistance The resistor that determines the oscillation frequency is connected between this pin and GND.
16	Ст	Timing capacitance The capacitor that determines the oscillation frequency is connected between this pin and GND. This pin outputs a triangle wave.

#### 2. ELECTRICAL SPECIFICATIONS

#### Absolute Maximum Ratings (Unless otherwise specified, T<sub>A</sub> = 25°C)

Parameter	Symbol	μΡC1909CX	μPC1909GS	Unit
Power Supply Voltage	Vcc	2	6	V
Output Current (DC, per output)	IC (DC)	1(	00	mA
Output Current (peak, per output)	IC (peak)	1.	.2	А
Total Power Dissipation	Power Dissipation PT 1000 694		694	mW
Operating Ambient Temperature	TA	–20 t	o +85	°C
Operating Junction Temperature	TJ	-20 to	o +150	°C
Storage Temperature	Tstg	-55 to +150 °C		

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

#### **Recommended Operating Conditions**

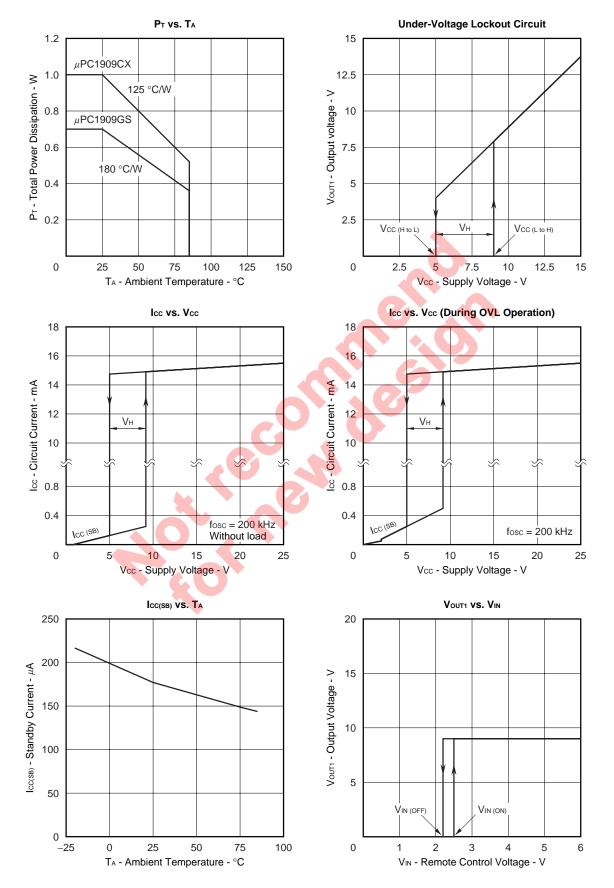
	Parameter	Symbol	MIN.	TYP.	MAX.	Unit
	Power Supply Voltage	Vcc	7	10	24	V
	Oscillation Frequency	fosc	50	200	500	kHz
	Output Load Capacitance	C∟	5	2200	3000	pF
★	Timing Resistance	RT	10			kΩ
	Operating Junction Temperature	TJ	-20		+100	°C

\* Caution The recommended operating range may be exceeded without causing any problems provided that the absolute maximum ratings are not exceeded. However, if the device is operated in a way that exceeds the recommended operating conditions, the margin between the actual conditions of use and the absolute maximum ratings is small, and therefore thorough evaluation is necessary. The recommended operating conditions do not imply that the device can be used with all values at their maximum values.

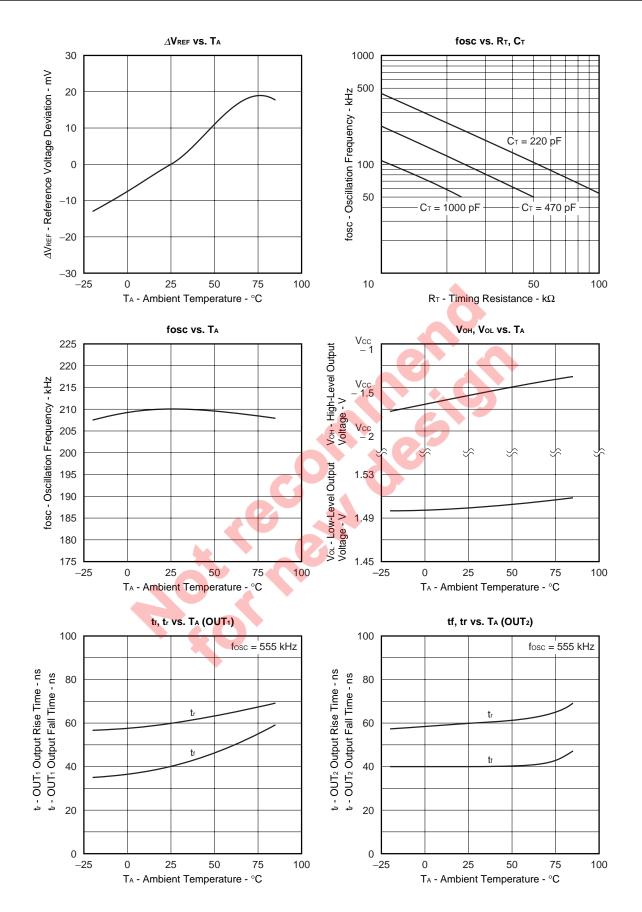
Block	Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Total	Standby Current	ICC (SB)	Vcc = 7 V		0.1		mA
	Circuit Current	lcc	Without load	6	12	18	mA
Under-	Startup Threshold Voltage	VCC (L to H)		8	9	10	V
Voltage Lockout Circuit	Operating Voltage Hysteresis Width	Vн		3	4	5	V
Reference	Output Voltage	Vref	Iref = 0 A	4.7	4.9	5.1	V
Voltage	Line Regulation	REGIN	8 V ≤ Vcc ≤ 15 V, Iref = 0 A		1	10	mV
	Load Regulation	REG∟	$1 \text{ mA} \leq I_{\text{REF}} \leq 4 \text{ mA}$		6	12	mV
	Output Voltage Temperature Coefficient	$\Delta V_{REF} / \Delta T$	$-10^{\circ}C \le T_A \le +85^{\circ}C$ , Iref = 0 A		400	(700)	μV/°C
	Short Circuit Current	O short	Iref = 0 A		15		mA
Oscillation	Oscillation Frequency	fosc		180	200	220	kHz
	Frequency Line Regulation	∆f/∆V	8 V $\leq$ Vcc $\leq$ 15 V		1		%
	Frequency Temperature Coefficient	∆f/∆T	–10°C ≤ T₄ ≤ +85°C		2	(5)	%
PWM	Input Bias Current	Ів (сомр1)	VCOMP1 = VREF			10	μA
Comparator		IB (COMP2)	VCOMP2 = VREF			10	μA
	Low-level Threshold Voltage	VTH (L)			1.5		V
	High-level Threshold Voltage	Vтн (н)			3.5		V
	Dead time Temperature Coeficient	ΔΟΤ/ΔΤ	–10°C ≤ Ta ≤ +85°C, Vd = 0.46 Vref		3		%
Output	Low-level Output Voltage	Vol	ISINK = 3 mA			0.5	V
	High-level Output Voltage	Vон	ISOURCE = 30 mA		Vcc - 1.6		V
	Rise Time	tr	$R_L$ = 15 $\Omega$ , $C_L$ = 2200 pF		60		ns
	Fall Time	tr	$R_L$ = 15 Ω, $C_L$ = 2200 pF		40		ns
Remote	Input Voltage at Output ON	VIN (ON)		2.4	2.6	2.8	V
Control	Input Voltage at Output OFF	VIN (OFF)		2.2	2.4	2.6	V
	Hysteresis Width	Vн		0.1	0.2	0.3	V
Overcurrent	Overcurrent Threshold Voltage	VTH (OC)		190	210	230	mV
Latch	Input Bias Current	B (OC)	Vcc = 0 V		200		μA
	Delay to Output	td (OC)			150		ns
Overvoltage	Overvoltage Threshold Voltage	Vth (ov)		2	2.4	2.8	V
Latch	Input Bias Current	IB (OV)	Vov = Vref			4	μA
	OVL Reset Voltage	VR (OV)			2		V
	Delay to Output	td (OV)			750		ns

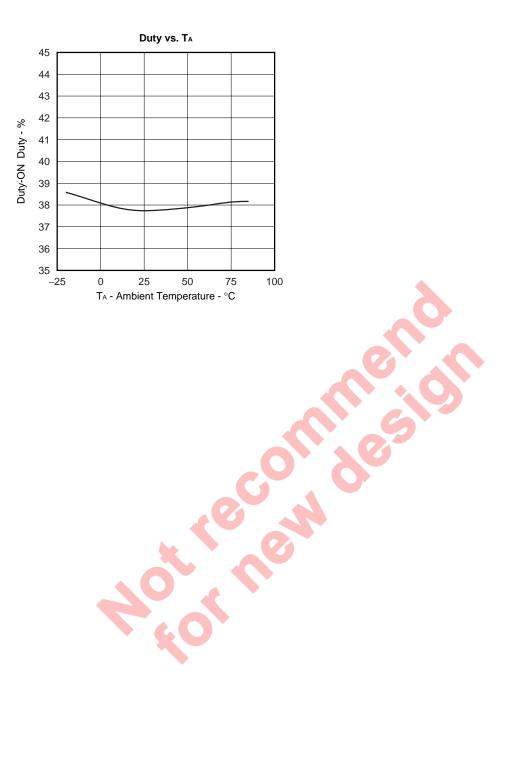
#### Electrical Characteristics (Unless otherwise specified, $T_A = 25^{\circ}C$ , $V_{CC} = 10 V$ , $R_T = 10 k\Omega$ , fosc = 200 kHz)

**Remark** Values in parentheses () represent reference values.



Typical Characteristics Curves (Unless otherwise specified, T<sub>A</sub> = 25°C, V<sub>CC</sub> = 10 V, Reference Values)



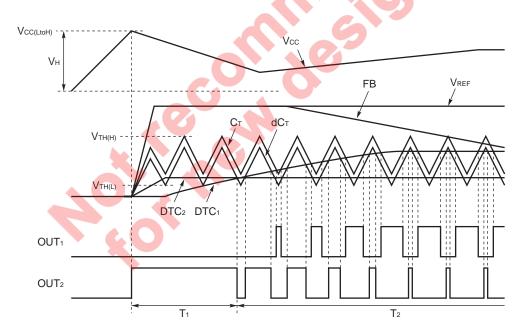


#### **\* 3. OPERATION OVERVIEW**

#### 3.1 Startup

The operating waveforms at startup are shown in Figure 3-1 below. The operations at startup are as follows.

- <1> When the power supply voltage (Vcc) rises and exceeds the starting voltage (Vcc(L to H)), the reference voltage (VREF) rises.
- <2> The DTC1 voltage is boosted as the soft start capacitor is charged (refer to 4.5.3 Soft start).
- <3> Because the DTC1 voltage is at a lower potential than other voltages, OUT1 and OUT2 become low and high level respectively during the T1 period.
- <4> If the DTC1 voltage is further boosted so that there is a period in which it is higher than the dCτ voltage in the T2 period, OUT2 becomes low level. In the period in which the DTC1 voltage exceeds CT, OUT1 and OUT2 are high and low level respectively. The duty of OUT1 increases and that of OUT2 decreases as DTC1 is boosted.



#### Figure 3-1. Waveforms at Startup

Signal Name	Function	Signal Name	Function
OUT <sub>1</sub>	Output for main switch	OUT <sub>2</sub>	Output for subswitch
DTC <sub>1</sub>	Voltage for setting maximum duty limit of OUT1	DTC <sub>2</sub>	Voltage for setting maximum duty limit of OUT2
FB	Feedback voltage of converter output	Ст	Triangle wave generated by oscillator
dC⊤	Triangle wave that is $C_{\ensuremath{T}}$ level-shifted via the		
	level shift circuit (OLS)		

- Remarks 1. The oscillation frequency of CT is determined by the external capacitor connected to the CT pin and the external resistor connected to the RT pin (refer to 3.3 Overcurrent Limitation Operation). CT is a symmetrical triangle wave with a trough voltage (low-level threshold voltage VTH(L)) of 1.5 V and a crest voltage (high-level threshold voltage VTH(H)) of 3.5 V. Note that the dCT voltage cannot be viewed externally.
  - 2. In the T1 and T2 periods in Figure 3-1, the FB voltage level rises as the converter output voltage is boosted, with the result that the converter voltage cannot be controlled by FB.

Data Sheet G14309EJ2V0DS00

#### 3.2 Steady Operation

The operating waveforms during steady operation are shown in Figure 3-2 below. Steady operation as used here refers to the state in which the overcurrent and overvoltage latches are not working. The operations that occur during steady operation are as follows.

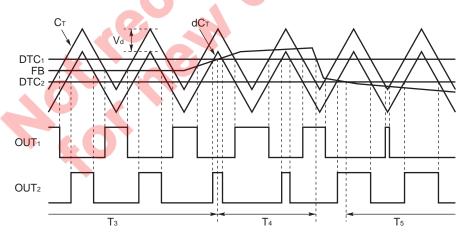
<1> When the converter is operating at the rated input and output, the FB voltage is between DTC<sub>1</sub> and DTC<sub>2</sub> (in the T<sub>3</sub> period in Figure 3-2).

•The FB voltage and CT triangle wave are compared by PWM comparator 1. OUT<sub>1</sub> is high level when the FB voltage is higher than the CT voltage.

•The FB voltage and level-shifted dCT triangle wave are compared by PWM comparator 2. OUT<sub>2</sub> is high level when the FB voltage is lower than the dCT voltage.

- <2> Because the input voltage becomes lower as the load of the converter is increased, there is a period when the FB voltage rises and the OUT1 duty increases (the T4 period in Figure 3-2). When the FB voltage is greater than the DTC1 voltage, OUT1 operates at the maximum duty determined by DTC1. At this time also, OUT2 operates at the minimum duty determined by DTC1.
- <3> Because the input voltage becomes higher as the load of the converter is decreased, there is a period when the FB voltage falls and the OUT1 duty decreases (the T5 period in Figure 3-2).

When the FB voltage is less than the DTC<sub>2</sub> voltage, OUT<sub>2</sub> operates at the maximum duty determined by DTC<sub>2</sub>.



#### Figure 3-2. Waveforms During Steady Operation

## NEC

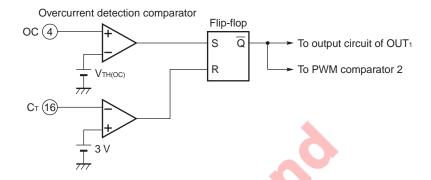
For the dC<sub>T</sub> level shift amount and the OUT<sub>1</sub> and OUT<sub>2</sub> dead time settings, refer to **4.4 Dead Time Setting**. The relationship between the FB, DTC<sub>1</sub>, and DTC<sub>2</sub> voltages in each operating state and the pins that determine the duty of OUT<sub>1</sub> and OUT<sub>2</sub> are shown in Table 3-1 below. For the duty settings, refer to **4.5 Duty Settings**.

Operating Status		Voltage Relationship	Pin That Determines OUT1 Duty	Pin That Determines OUT <sub>2</sub> Duty
Steady operation 1 (rated status)	T₃	$DTC_2 < FB < DTC_1$	FB	FB
Steady operation 2 (heavy load, low input)	T4	DTC <sub>2</sub> < DTC <sub>1</sub> < FB	DTC1	DTC <sub>1</sub>
Steady operation 3 (light load, high input)	T₅	FB < DTC <sub>2</sub> < DTC <sub>1</sub>	FB	DTC <sub>2</sub>

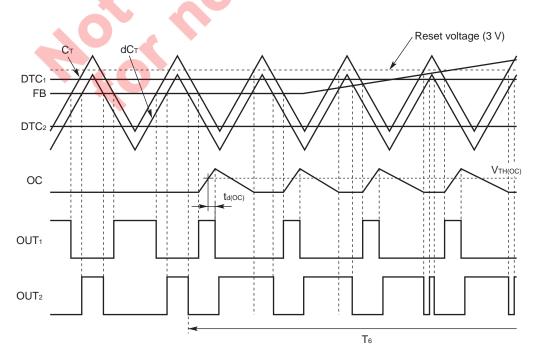
#### 3.3 Overcurrent Limitation Operation

The internal configuration of the overcurrent latch circuit is shown in Figure 3-3 below.





If a voltage that exceeds the overcurrent detection voltage ( $V_{TH(OC)} = 210 \text{ mV TYP.}$ ) is input to the OC pin, OUT<sub>1</sub> is latched to low level, and then OUT<sub>2</sub> is latched to high level. The time between the detection of overcurrent and when OUT<sub>1</sub> becomes low level is the overcurrent detection delay time. Moreover, if the voltage of the CT pin exceeds 3.0 V, the reset signal will be input to the flip-flop, and the latch status of OUT<sub>1</sub> and OUT<sub>2</sub> will be reset. When the OC pin voltage reaches the overcurrent detection voltage, even in the cycle in which the latch status was reset, the latch and reset operations will be repeated. In other words, the pulse width is limited every cycle (pulse-by-pulse current limitation). The waveforms when overcurrent limitation is operating are shown in Figure 3-4 below.

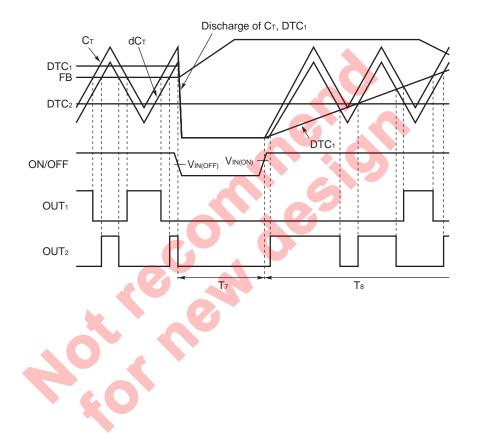


#### Figure 3-4. Waveforms When Overcurrent Limitation Is Operating

#### 3.4 On/Off Operation

The output of  $OUT_1$  and  $OUT_2$  can be made low level (off) by making the voltage of the ON/OFF pin low level. This also causes discharge of the soft start capacitor externally connected to the DTC<sub>1</sub> pin and the timing capacitor externally connected to the CT pin.

To prevent chattering when turning on and off slowly, the threshold voltage of the ON/OFF pin has a 0.2-V hysteresis. The waveforms during the on/off operation are shown in Figure 3-5 below.



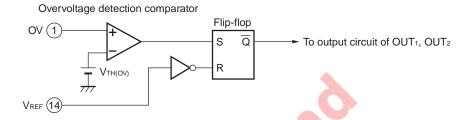
#### Figure 3-5. Waveforms During On/Off Operation

#### 3.5 Overvoltage Protection Operation

The overvoltage latch circuit is a protection circuit that stops the power supply to prevent damage to the load after detection of overvoltage caused by abnormal boosting of the output of the converter.

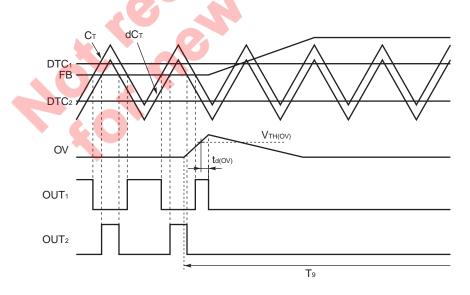
The internal configuration of the overvoltage latch circuit is shown in Figure 3-6 below.

#### Figure 3-6. µPC1909 Overvoltage Latch Circuit



The threshold voltage (VTH(OV)) connected to the overvoltage detection comparator is 2.0 to 2.8 V (2.4 V TYP.). If the voltage of the OV pin exceeds VTH(OV), OUT1 and OUT2 are latched to low level. The waveforms when OV (overvoltage) occurs are shown in Figure 3-7 below.

To reset the status of the overvoltage latch, drop the voltage of the Vcc pin to below the OVL release voltage ( $V_{R(OV)} = 2 V TYP$ .), and drop the voltage of the V<sub>REF</sub> pin to a sufficiently low level.



#### Figure 3-7. Waveforms When Overvoltage Latch Is Operating

#### **\*** 4. SETTINGS

#### 4.1 Controller Settings

The feedback circuit for when the converter output voltage is detected on the secondary side is configured as shown in Figure 4-1 below. The feedback gain is primarily determined by the R<sub>1</sub> resistor.

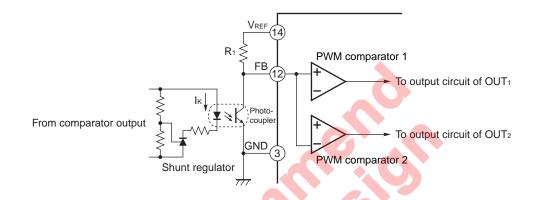


Figure 4-1. Feedback Circuit Configuration

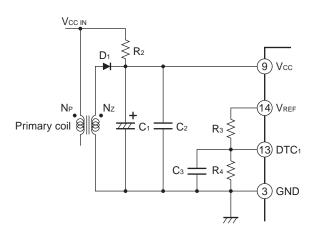
The voltage of the FB pin is input to PWM comparators 1 and 2.

During steady operation ( $DTC_2 < FB < DTC_1$ ), the duty of  $OUT_1$  and  $OUT_2$  is determined by the slice level of the triangle wave based on the FB pin voltage.

- Caution When using a shunt regulator such as the  $\mu$ PC1093 for the secondary-side detector, Ik must be set bearing in mind the variation of the CTR in the photocoupler. Also, be sure to use the photocoupler grounded at the emitter ground.
- 4.2 Startup Circuit, Low Voltage Malfunction Prevention Circuit Settings

The startup circuit is configured as shown in Figure 4-2 below.

#### Figure 4-2. Startup Circuit



In the  $\mu$ PC1909, when the power supply voltage (Vcc) rises but is less than the operation start voltage (Vcc(L to H)), a current of about 100  $\mu$ A flows as a standby current.

When Vcc reaches or exceeds Vcc(L to H), the internal reference voltage (VREF) rises and operating current is supplied to the internal circuits, increasing the circuit current (Icc) to a level of about 12 mA.

In the startup circuit in Figure 4-2,  $I_{CC(SB)}$  is supplied via a startup resistor (R<sub>2</sub>), and when the power MOS FET is turned on after the  $\mu$ PC1909 is started up, Icc is supplied from a capacitor (C<sub>1</sub>) until voltage reaches the auxiliary coil. R<sub>2</sub> is determined using Icc(SB) as follows.

 $R_2 \leq \left\{ \frac{V_{IN(MIN.)} - V_{CC(LtoH)(MAX.)}}{I_{CC(SB)(MAX.)} + I_{REF}} \right\}$ 

If R<sub>2</sub> is too small, the loss via R<sub>2</sub> during steady operation will be large. The loss via R<sub>2</sub> during steady operation ( $P_{L(MAX,)}$ ) is shown below. In this equation, N<sub>z</sub> is the number of turns in the power supply auxiliary coil, N<sub>P</sub> is the number of turns in the primary coil, and V<sub>F(D1)</sub> is the forward direction voltage drop in the diode (D1).

$$P_{L(MAX.)} = \frac{\{(1 - Nz/NP) \cdot V_{IN(MAX.)} + V_{F(D1)}\}^2}{R_2}$$

Note that a film or other capacitor (C<sub>2</sub>) with good high-frequency characteristics should be connected to prevent a high-frequency current flowing through the Vcc line when the power MOS FET is driven.

To apply a soft start, connect a soft start capacitor (C<sub>3</sub>) between the DTC<sub>1</sub> pin and GND. Using the overcurrent limitation function of the OC pin allows the duty to be limited on a pulse-by-pulse basis, enabling a more secure soft start. The time between the startup of the  $\mu$ PC1909 and the first output of OUT<sub>1</sub> (t<sub>1</sub>) is expressed as follows.

$$t_{1} = -\frac{C_{3} \cdot R_{3}}{1 + R_{3} / R_{4}} \ln \{1 - (1 + R_{3} / R_{4}) \cdot (V_{TH(L)} / V_{REF})\}$$

Although Vcc drops in the t1 period, C1 is determined so that OUT1 is output while the drop voltage has not fallen to the operating voltage hysteresis width VH. At this time, because OUT2 is output before OUT1 (refer to **3.1 Startup**), C1 must be set to compensate for the increase in current caused by the output of OUT2. Refer to Figure 3-1. Waveforms at Startup for the operating waveforms.

$$C_1 > \frac{I_{CC} + I_{REF} + I_{OUT} - I_{CC(R)}}{V_H} \cdot t_1$$

Here, IREF is the current that flows through the resistor with the maximum duty setting connected to the VREF pin, IOUT is the power MOS FET drive current, and ICC(R) is the current that is supplied from the startup resistor (R<sub>2</sub>).

Note that when the rising of V<sub>REF</sub> is later than the rising of V<sub>CC</sub> at startup, OUT<sub>1</sub> and OUT<sub>2</sub> become high level simultaneously when V<sub>REF</sub> is in a range of about 0.45 to 0.5 V, which may result in the external power MOS FET being inadvertently turned on. To prevent this, speed up the rising of V<sub>REF</sub> by pulling it up to V<sub>CC</sub> with a resistor. Note, however, that the standby current (I<sub>CC(SB)</sub>) will increase by only the current that flows through the connected resistor.

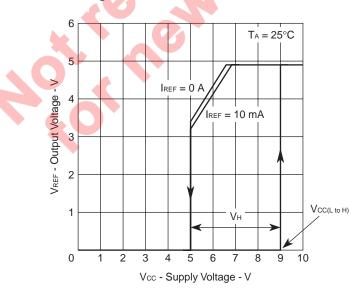
The pull-up resistance value (R) can be calculated from the following equation.

$$\mathsf{R} [k\Omega] = \frac{\mathsf{V}_{\mathsf{CC}(\mathsf{MAX.})} [\mathsf{V}] - 0.5}{0.1 [\mathsf{mA}]}$$

Remark Vcc(MAX.): The highest power supply voltage that can be applied at startup without causing malfunction.

For the same reason, if Vcc drops below the operation stopped voltage (Vcc(L to H) – VH), VREF and the constant current circuit will be cut-off, which weakens the drive capacity of the OUT<sub>1</sub> and OUT<sub>2</sub> outputs when the power supply is cut-off. If this drive capacity is weakened, the charge that has accumulated at the power MOS FET gates may not be sufficiently discharged, blunting the falling section of the power MOS FET gate drive waveform. In this case, connecting a capacitor of at least 0.47  $\mu$ F between the VREF pin and GND allows sufficient time and output block drive capacity to discharge the charge accumulated at the gates of the power MOS FET.

Because the operation start and stop voltages in the  $\mu$ PC1909 are 9 V TYP. and 5 V TYP. respectively, VREF is output while operation is stopped until Vcc is 5 V or lower. However, when Vcc reaches about 6.5 V, VREF falls together with Vcc, as can be seen in Figure 4-3. When VREF falls, the constant current value of the triangle wave oscillator decreases, causing the oscillation frequency to drop.

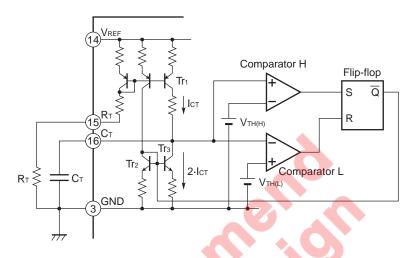




In standard applications, VREF is resistance-divided to create the DTC1, DTC2, and FB voltages. In addition, because the levels of the triangle wave (CT) and internally level-shifted triangle wave (dCT) are also generated internally by dividing the resistance of VREF, if VREF drops, each of the above will drop in proportion to VREF. As a result, even if the oscillation frequency drops, standard applications are not affected. Further study will be required, however, including for transient states.

#### 4.3 Oscillator Settings

The oscillator circuit is shown in Figure 4-4 below.



#### Figure 4-4. µPC1909 Oscillator Circuit

A timing resistor ( $R_T$ ) is connected between the  $R_T$  pin and GND, and a timing capacitor ( $C_T$ ) is connected between the  $C_T$  pin and GND. The charge/discharge current of  $C_T$  is determined by  $R_T$ . The oscillator operates as follows.

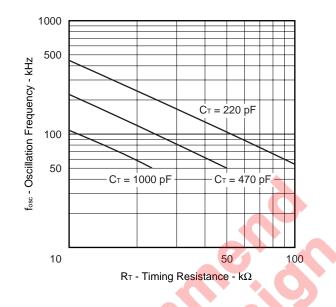
- <1> If Ict is taken as the current that flows through Tr1, the current the flows through Tr3 is set as 2 x Ict. Because the flip-flop ( $\overline{Q}$ ) outputs a high level at startup, Tr2 is off, and Ct is charged with Ict.
- When the CT voltage reaches VTH(H) = 3.5 V TYP., the output of comparator H is inverted, and Tr2 is turned on. Due to the discharging of the current set by 2 x lct, the current flowing through CT is (lct – 2 x lct) = – lct, so CT is discharged by lct.
- <3> If the CT voltage drops to VTH(L) = 1.5 V TYP., the output of comparator L is inverted, the flip-flop is reset, and CT is recharged because Tr2 is off.
- <4> <2> and <3> are repeated, generating a triangle wave with an amplitude of 1.5 to 3.5 V.

The oscillation frequency can be approximated from the following equation.

 $\label{eq:fosc} \text{fosc} \cong \frac{1 \times 10^6}{0.8251 \times \text{CT} \; [\text{pF}] \times (\text{RT} \; [\text{k}\Omega] + 0.8) + 320} \; [\text{kHz}]$ 

The results of measuring fosc vs. R⊤ are shown in Figure 4-5 below, with C⊤ as the parameter.





#### 4.4 Dead Time Setting

The period in which OUT<sub>1</sub> and OUT<sub>2</sub> are simultaneously off is called dead time. This is an important parameter to realize a zero-cross switch when active-clamping. To set the dead time, it is necessary to adjust both the oscillation frequency and level shift parameters (for details of the oscillation frequency setting, refer to **4.3 Oscillator Settings**).

#### 4.4.1 Level shift setting

Whichever is higher of the DTC<sub>2</sub> pin and FB pin voltages is compared with the triangle wave that is the internally levelshifted wave of the C<sub>T</sub> pin (dC<sub>T</sub>). OUT<sub>2</sub> is high level while dC<sub>T</sub> is higher than the DTC<sub>2</sub> and FB voltages.

The triangle wave dC<sub>T</sub>, which controls OUT<sub>2</sub>, is generated by internally level-shifting the C<sub>T</sub> wave on the low potential side. The amount of shift (V<sub>d</sub>) is determined using the resistor (R<sub>CT2</sub>) connected between the C<sub>T2</sub> and V<sub>REF</sub> pins. V<sub>d</sub> can be calculated from the following equation.

$$V_{d} \cong \frac{2 \times 4.2}{R_{CT2} [k\Omega] + 10} [V]$$

A general diagram of the level shift circuit (OLS) is shown in Figure 4-6, and the relationship between the oscillation frequency (fosc), the dead time (tqd), and resistor RCT2 is shown in Figure 4-7.

Figure 4-6. µPC1909 Level Shift Circuit (OLS)

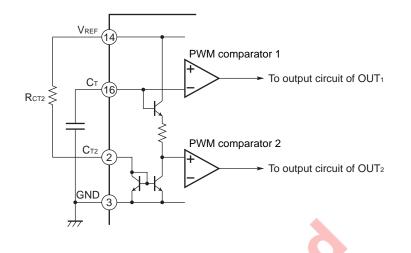
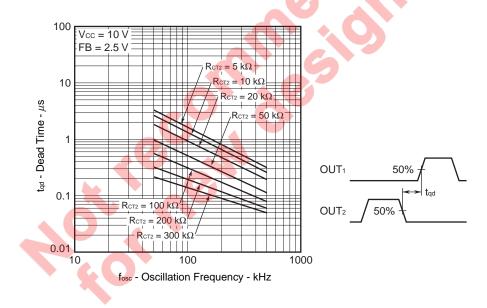


Figure 4-7. Relationship Between fosc, tgd and RcT2

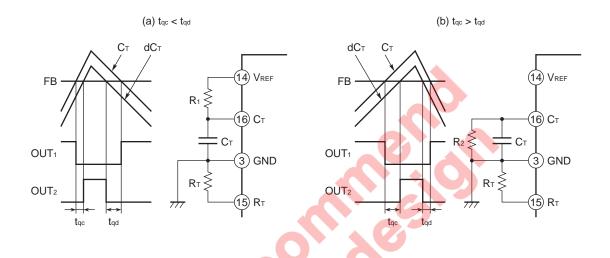


#### 4.4.2 Dead time adjustment

The dead time between the fall of  $OUT_1$  and the rise of  $OUT_2$  (t<sub>qc</sub>) and the dead time between the fall of  $OUT_2$  and the rise of  $OUT_1$  (t<sub>qd</sub>) is determined by the oscillation frequency and the amount of level shift of the triangle wave.

Although usually  $t_{qc} = t_{qd}$ , if these values differ, connect a suitable resistor between the CT pin and the VREF pin, as well as between the CT pin and GND, and adjust the dead time by making the oscillation waveform asymmetrical, as shown in Figure 4-8.

#### Figure 4-8. Dead Time Adjustment



The charge current ( $I_{CT}$ ) of the timing capacitor ( $C_T$ ) is expressed as follows.

Ict [A] = 
$$\frac{4.2}{800 + RT[\Omega]}$$

If RT is taken as 20 k $\Omega$ , Ict will be approximately 200  $\mu$ A.

To reduce  $t_{qc}$ , connect a resistor (R<sub>1</sub>) between the V<sub>REF</sub> and C<sub>T</sub> pins. If the value of the resistor is set so that the current charged in C<sub>T</sub> is about 10% more than lc<sub>T</sub>,  $t_{qc}$  can be reduced and  $t_{qd}$  increased by about 10% compared to when R<sub>1</sub> is not connected.

R<sub>1</sub> here can be calculated from the following equation.

$$\mathsf{R}_{1} \left[ \Omega \right] = \frac{\mathsf{V}_{\mathsf{REF}} \left[ \mathsf{V} \right] - \mathsf{V}_{\mathsf{OSC}} \left[ \mathsf{V} \right]}{\varDelta \mathsf{Ict} \left[ \mathsf{A} \right]}$$

Remark Vosc: Central voltage value of triangle wave

 $\Delta$ Ict: Value of Ict current increased (decreased) by R<sub>1</sub> (R<sub>2</sub>)

Note also that connecting a resistor (R<sub>2</sub>) between  $C_T$  and GND makes it possible to reduce the current charged to  $C_T$ . If a resistor is selected that allows about 10% current to flow,  $t_{qc}$  can be increased and  $t_{qd}$  reduced by about 10% compared to when R<sub>2</sub> is not connected.

 $R_2$  here can be calculated from the following equation.

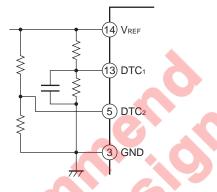
$$\mathsf{R}_{2}\left[\Omega\right] = \frac{\mathsf{Vosc}\left[\mathsf{V}\right]}{\varDelta\mathsf{Ict}\left[\mathsf{A}\right]}$$

#### 4.5 Duty Settings

#### 4.5.1 Maximum duty setting

In the steady operation state (DTC<sub>2</sub> < FB < DTC<sub>1</sub>), the duty during operation at the FB voltage is determined by OUT<sub>1</sub> and OUT<sub>2</sub>. To set the duty as an independent FB input at times such as at startup, during low voltage input, and when the current is limited, the OUT<sub>1</sub> and OUT<sub>2</sub> outputs must be set to their maximum duty values. Set the maximum duty for OUT<sub>1</sub> and OUT<sub>2</sub> via the DTC<sub>1</sub> and DTC<sub>2</sub> pins, respectively, as shown in Figure 4-9.

#### Figure 4-9. Maximum Duty Settings in µPC1909



Note that when pulse-by-pulse current limitation is being applied using the OC pin, the maximum duty of OUT<sub>1</sub> should be set to between 60 and 65%. This is because the duty conversion of OUT<sub>1</sub> sets the reset level of the internal OC circuit to about 75%. For details, refer to **4.7 Overcurrent Limiter Settings**.

There is no limit to the maximum duty of OUT<sub>2</sub>.

#### 4.5.2 Minimum duty limit

When  $OUT_1$  is operating at maximum duty, if  $OUT_2$  is not output, it may inadvertently be set to a duty of 0%, depending on the value of " $OUT_1$  ON time + t<sub>qc</sub> + t<sub>qd</sub>". If  $OUT_2$  has 0% duty when active clamping, the transformer will not be able to be reset, and a minimum duty limit will have to be set for  $OUT_2$  at the same time the maximum duty of  $OUT_1$  is determined. Because the DTC1 pin is also the input of PWM comparator 2 on the  $OUT_2$  side, if the FB voltage is higher than the DTC1 voltage, the DTC1 voltage is compared with dCT and the minimum duty of  $OUT_2$  is limited.

#### 4.5.3 Soft start

This IC incorporates a transistor for discharging the soft start capacitor connected between the DCT<sub>1</sub> pin and GND. If Vcc falls below the operation stopped voltage (5 V TYP.) or if the ON/OFF pin becomes low level (off), the DTC<sub>1</sub> pin becomes low level and the soft start capacitor is initialized.

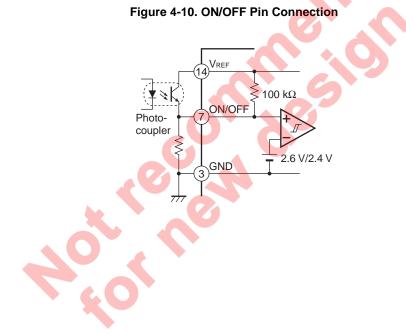
There is no such transistor incorporated on the DTC<sub>2</sub> side.

#### 4.6 Remote Control

In the  $\mu$ PC1909, starting up and stopping a converter can be controlled by turning on and off the output circuit using an external signal. When the ON/OFF pin is made low level, the low voltage malfunction protection circuit operates and cuts off OUT<sub>1</sub> and OUT<sub>2</sub>, causing the timing capacitor connected between the C<sub>T</sub> pin and GND (C<sub>T</sub>) and the soft start capacitor connected between the DTC<sub>1</sub> pin and GND to discharge. Because the on/off threshold voltage has 0.2-V hysteresis, the occurrence of chattering can be suppressed, even in slow on/off operations.

The ON/OFF pin is internally pulled up to VREF via a 100 k $\Omega$  resistor. When the on/off function is not used, however, be sure to connect the ON/OFF pin directly to the VREF pin in order to prevent the occurrence of noise.

A configuration whereby on/off control is controlled from the primary side by a photocoupler is shown in Figure 4-10 below. Be sure to set the pull-down resistor connected to the ON/OFF pin so that the leakage current between C and E when the photocoupler is off does not cause the ON/OFF pin voltage to be boosted to a level whereby the  $\mu$ PC1909 is turned on.



#### 4.7 Overcurrent Limiter Settings

The OC pin in the  $\mu$ PC1909 allows the realization of a pulse-by-pulse overcurrent limiter, whose configuration is shown in Figure 4-11 below.

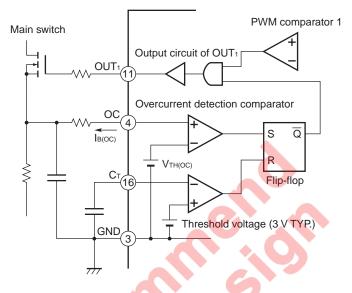


Figure 4-11. µPC1909 Overcurrent Limiter

If overcurrent is detected by the overcurrent detection comparator, OUT1 is latched to low level by the flip-flop. Moreover, if the triangle wave generated by the oscillator and a voltage with a threshold value that causes the output latch to be reset are input to the other comparator the flip-flop will be reset at each cycle.

Because the reset threshold voltage is internally set to 3 V TYP. (about 75% VREF), if a maximum duty of 75% or over is set by the DTC1 pin thus activating overcurrent limitation by the OC pin, two pulses will be inadvertently output in one cycle. To allow for differences in ICs, do not set the maximum duty of DTC1 (60% or over) to more than 65% when applying overcurrent limitation using the OC pin. Alternatively, do not use OC pin overcurrent limitation if setting the maximum duty (60% or over) to more than 65%. In this case (overcurrent limitation current not used), connect the OC pin directly to GND.

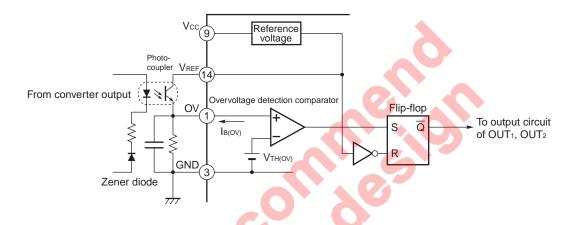
Discharge current flows through the OC pin. This discharge current is expressed as the input bias current of the overcurrent latch block ( $I_{B(OC)}$ ). Although a filter is attached to the OC pin to prevent the overcurrent latch circuit from malfunctioning due to the surge current that flows when the power MOS FET is turned on, be sure to set the resistor to no more than 100  $\Omega$  to stop  $I_{B(OC)}$  causing a shift in the overcurrent detection point.

When overcurrent is being limited by the OC pin, OUT<sub>1</sub> operates at the minimum pulse width limitable by the overcurrent latch circuit. The minimum pulse width is the sum of the  $\mu$ PC1909's overcurrent detection delay time (td(oc)), the delay of the filter attached to the OC pin, and the turn-on time of the power MOS FET.

During steady operation (DTC<sub>2</sub> < FB < DTC<sub>1</sub>), OUT<sub>2</sub> operates at the duty determined by the FB voltage. Because the FB voltage rises when the output of the converter drops, the duty of the OUT<sub>2</sub> output drops in line with the converter output, until it reaches the minimum duty set by the DTC<sub>1</sub> voltage.

#### 4.8 Overvoltage Protection Circuit Setting

The overvoltage protection circuit based on the overvoltage latch in the  $\mu$ PC1909 is configured as shown in Figure 4-12 below. The threshold voltage connected to the overvoltage detection comparator (VTH(OV)) is 2.0 to 2.8 V (2.4 V TYP.). If the input at the OV pin exceeds VTH(OV), the flip-flop in the IC latches OUT1 and OUT2 to low level. Once the overvoltage latch circuit is latched, it is not released until the power supply voltage of the IC (Vcc) falls below the OVL release voltage (2 V TYP.) (because Icc is higher than Icc(SB) when the circuit is latched, the operation status will not be restored in the steady input state).





Discharge current flows through the OV pin. This is the input bias current of the overvoltage latch block in the electrical specifications ( $I_{B(OV)} = 4 \ \mu A \ MAX$ .). To prevent the detection level fluctuating due to  $I_{B(OV)}$ , and to allow for the effect of the leakage current between C and E in the photocoupler, be sure to set the overvoltage detection resistor connected to the OV pin to no more than 100 k $\Omega$ .

Because the OVL (overvoltage latch) detection delay time is about 750 ns, a capacitor with good frequency characteristics should be connected between the OV pin and GND to prevent malfunction due to noise. However, if the overvoltage latch circuit does malfunction due to electrostatic discharge or other such external noise, an effective countermeasure is to connect a capacitor with good frequency characteristics such as a film capacitor between Vcc and GND.

Caution If the power is reapplied immediately after being stopped (VREF drop) while there is charge remaining in the filter's capacitor (such as when Vcc (auxiliary coil voltage) is being monitored from VREF without configuring an overvoltage protection circuit such as is shown in Figure 4-12), the overvoltage latch threshold value will be boosted in proportion with the boosting of VREF, possibly causing the overvoltage latch to latch too easily.

#### 4.9 Output Circuit

The output circuit is a totem-pole output with a peak output current rating ( $I_{C(peak)}$ ) of 1.2 A. Although a power MOS FET can be driven directly, be careful not to exceed the allowable loss of the  $\mu$ PC1909 when the input capacitance of the power MOS FET is large or the operating frequency is high. The switching speed of the power MOS FET is determined by the charge/discharge current of the gates and the charge of the power MOS FET's gates. Be sure, however, to insert a series resistor at the gates of the power MOS FET to avoid exceeding the peak output current rating of the  $\mu$ PC1909.

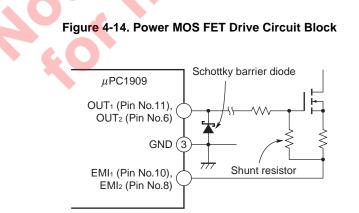
Note that the heat generated in the  $\mu$ PC1909 by the output current is determined by the charge at the gates of the power MOS FET, and is not related to the switching speed.

When the 2SK1954 is used, for example, the loss of the  $\mu$ PC1909 (Pd) can be determined as follows, when the gate drive voltage VGs  $\cong$  VOUT1 = 10 V and the oscillation frequency fosc = 200 kHz, as shown in the gate charge graph on the right (Figure 4-13):

> Pd = QG · VGS · fosc =10 [nC] x 10 [V] x 200 [kHz] =0.02 [W]

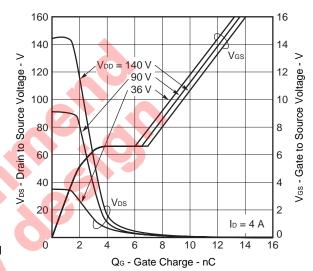
Moreover, when the  $\mu$ PC1909 and the power MOS FET are separated, the wiring from the OUT<sub>1</sub> and OUT<sub>2</sub> output pins is lengthened, which combined with the parasitic inductance and floating capacitance elements of the power MOS FET causes

the voltage of the OUT<sub>1</sub> and OUT<sub>2</sub> pins to fall below that of the GND pin (undershoot). In this case, clamp the undershoot by connecting a Schottky barrier diode as shown in Figure 4-14 to prevent the possibility of malfunction in the  $\mu$ PC1909.



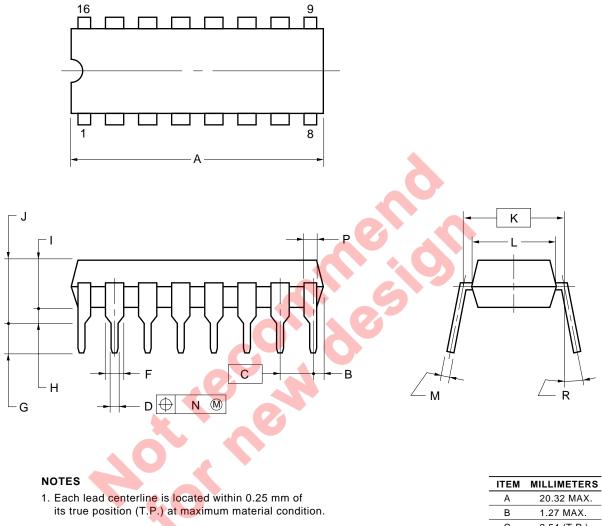
## Note that when active clamping, if the C-cut drive transistor is driven by OUT<sub>2</sub>, the voltage of the OUT<sub>2</sub> pin may become higher than Vcc. It is therefore vital to observe VOUT<sub>2</sub> $\leq$ Vcc + 5 V by taking action such as connecting a diode between OUT<sub>2</sub> and Vcc.

#### Figure 4-13. 2SK1954 Gate Change Characteristics



#### **\*** 5. PACKAGE DRAWINGS

### 16-PIN PLASTIC DIP (7.62mm(300))



2. Item "K" to center of leads when formed parallel.

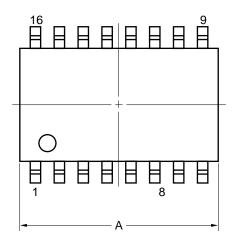
	WILLIWEIERS
А	20.32 MAX.
В	1.27 MAX.
С	2.54 (T.P.)
D	0.50±0.10
F	1.1 MIN.
G	3.5±0.3
н	0.51 MIN.
I	4.31 MAX.
J	5.08 MAX.
К	7.62 (T.P.)
L	6.5
М	$0.25\substack{+0.10 \\ -0.05}$
N	0.25
Р	1.1 MIN.
R	0~15°
	P16C-100-300B-2

-F

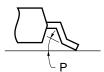
G

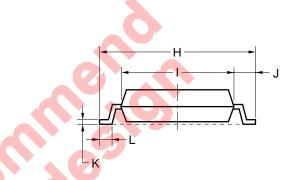
LΕ

## 16-PIN PLASTIC SOP (7.62 mm (300))



detail of lead end





#### NOTE

- D 🕀

Each lead centerline is located within 0.12 mm of its true position (T.P.) at maximum material condition.

 $\square$  N

<u>с</u> – С s

S

В

ITEM	MILLIMETERS
А	10.2±0.2
В	0.78 MAX.
С	1.27 (T.P.)
D	$0.42\substack{+0.08\\-0.07}$
E	0.1±0.1
F	1.65±0.15
G	1.55
Н	7.7±0.3
I	5.6±0.2
J	1.1±0.2
к	$0.22\substack{+0.08\\-0.07}$
L	0.6±0.2
М	0.12
N	0.10
Р	3° <sup>+7°</sup> -3°
	P16GM-50-300B-6

#### 6. RECOMMENDED SOLDERING CONDITIONS

When soldering this product, it is highly recommended to observe the conditions as shown below. If other soldering processes are used, or if the soldering is performed under different conditions, please make sure to consult with our sales offices.

For more details, refer to our document "SEMICONDUCTOR DEVICE MOUNTING TECHNOLOGY MANUAL"(C10535E).

#### Type of Through-hole Device

#### µPC1909CX: 16-pin plastic DIP (7.62 mm (300))

Soldering Method	Soldering Conditions
Wave soldering (pins only)	Solder bath temperature : 260°C MAX., Time : 10 seconds MAX.
Partial heating	Pin temperature : 300°C MAX., Time : 3 seconds MAX. (per pin)

## Caution For through-hole device, the wave soldering process must be applied only to leads, and make sure that the package body does not get jet soldered.

Type of Surface Mount Device

µPC1909GS: 16-pin plastic SOP (7.62 mm (300))

Soldering Method	Soldering Conditions	Recommended Condition symbol
Infrared reflow	Package peak temperature : 235°C, Time : 30 seconds MAX. (at 210°C or higher), Count : Twice or less	IR35-00-2
VPS	Package peak temperature : 215°C, Time : 40 seconds MAX. (at 200°C or higher), Count : Twice or less	VP15-00-2
Wave soldering	Soldering bath temperature : 260°C or less, Time : 10 seconds MAX., Count : Once, Preheating temperature : 120°C MAX. (package surface temperature)	WS60-00-1

Caution Do not use different soldering methods together.

[MEMO]



[MEMO]

[MEMO]



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  - "Specific": Aircraft, aerospace equipment, submersible repeaters, nuclear reactor control systems, life support systems and medical equipment for life support, etc.

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